



**SRAM MODULE 1Mbyte (256K x 32-Bit), 5V, 68-Pin JLCC Design**  
**Part No. HMS25632J2**

**GENERAL DESCRIPTION**

The HMS25632J2 is a high-speed static random access memory (SRAM) module containing 262,144 words organized in a x32-bit configuration. The module consists of two 256K x 16 SRAMs mounted on a 68-pin, double-sided, FR4-printed circuit board. The HMS25632J2 uses 31 common input and output lines and has an output enable pin which operates faster than address access time at read cycle. Also it allows that lower and upper byte access by data byte control (/BS0~/BS3). Output enable (/OE) and write enable(/WE) can set the memory input and output. Data is written into the SRAM memory when write enable (/WE) and chip enable (/CE) inputs are both LOW. Reading is accomplished when /WE remains HIGH and /CE and output enable (/OE) are LOW. For reliability, this SRAM module is designed as multiple power and ground pin. All module components may be powered from a single +5V DC power supply and all inputs and outputs are fully TTL-compatible.

**FEATURES**

- w Access times : 10, 12 and 15, 55ns
- w Low Power Dissipation
- w High-density 1Mbyte design
- w High-reliability, high-speed design
- w Single + 5V ±0.5V power supply
- w Easy memory expansion /CE and /OE functions
- w All inputs and outputs are TTL-compatible
- w Industry-standard pinout
- w FR4-PCB design
- w Low profile 68-pin JLCC

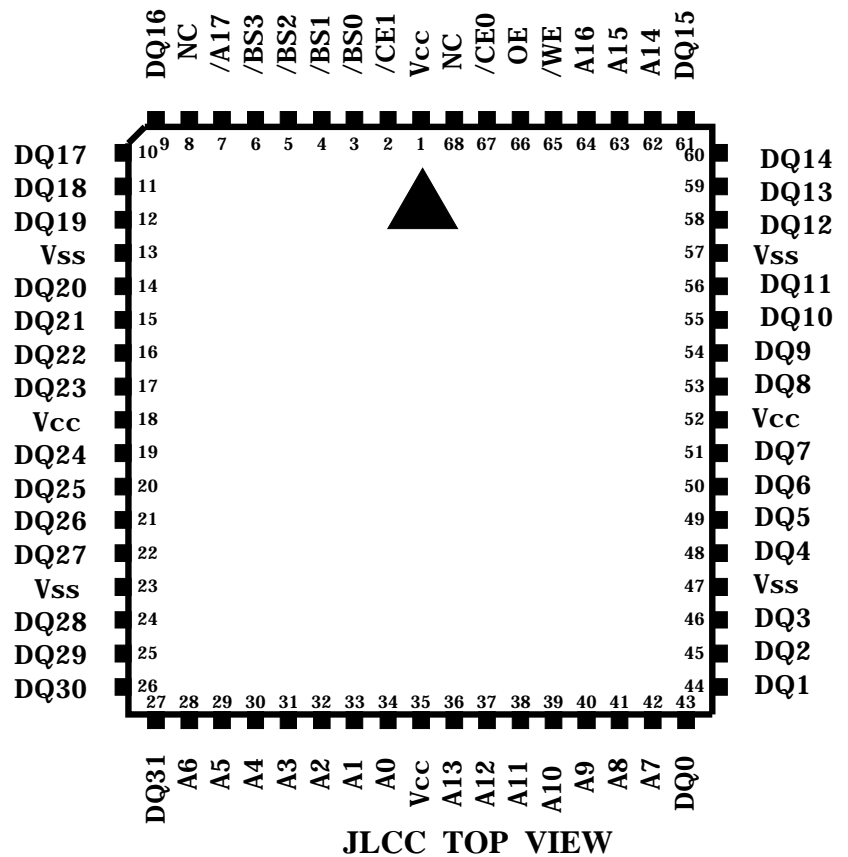
**OPTIONS**

- w Timing
  - 10ns access
  - 12ns access
  - 15ns access
- w Packages
  - 68-pin JLCC

**MARKING**

- 10
- 12
- 15
- J

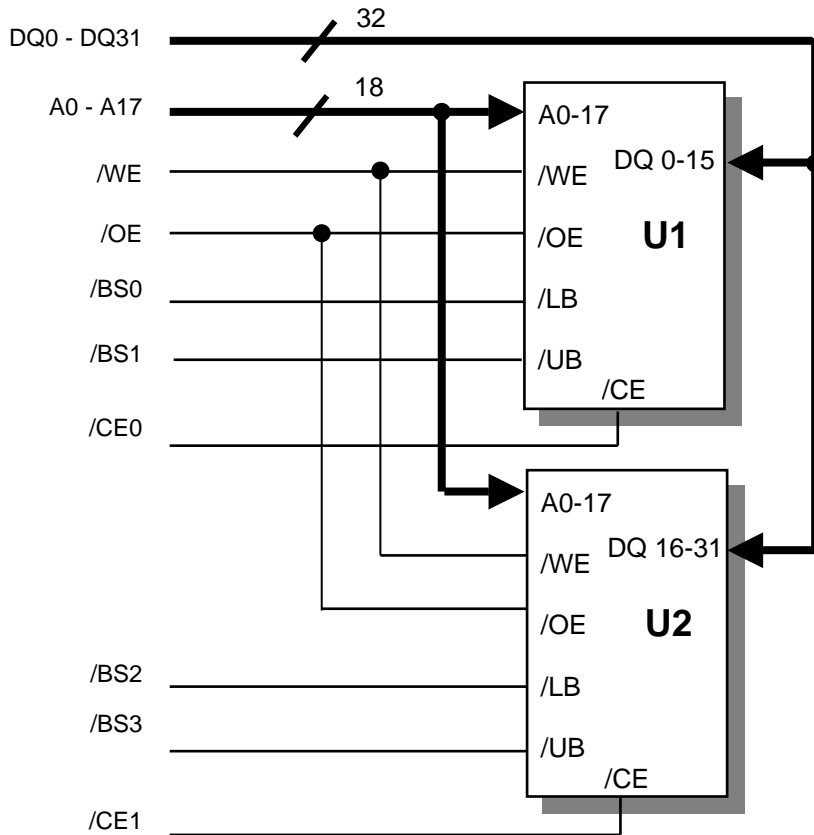
**PIN ASSIGNMENT**



**PIN FUNCTION**

PIN NAME	PIN FUNCTION	PIN NAME	PIN FUNCTION
A0-A17	Address Inputs	/BS0 ~ /BS3	Byte Controls
DQ0-31	Data Inputs	Vcc	Power(+5.0V)
/WE	Write Enable	Vss	Ground
/CE	Chip Enable	N.C	No Connection
/OE	Output Enable		

**FUNCTIONAL BLOCK DIAGRAM**



**ABSOLUTE MAXIMUM RATINGS**

PARAMETER	SYMBOL	RATING	
Voltage on Any Pin Relative to Vss	$V_{IN,OUT}$	-0.5V to +7.0V	
Voltage on Vcc Supply Relative to Vss	$V_{CC}$	-0.5V to +7.0V	
Power Dissipation	$P_D$	2W	
Storage Temperature	$T_{STG}$	-65°C to +150°C	
Operating Temperature	Commercial	$T_A$	0°C to +70°C
	Industrial	$T_A$	-40°C to +85°C

w Stresses greater than those listed under " Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operating section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

**RECOMMENDED DC OPERATING CONDITIONS** ( $T_A=0$  to  $70$  °C)

PARAMETER	SYMBOL	MIN	TYP.	MAX
Supply Voltage	$V_{CC}$	4.5V	5.0V	5.5V
Ground	$V_{SS}$	0	0	0
Input High Voltage	$V_{IH}$	2.2	-	$V_{CC}+0.5V^{**}$
Input Low Voltage	$V_{IL}$	-0.5*	-	0.8V

\*  $V_{IL}(\text{Min.}) = -2.0V$  (Pulse Width  $\leq 10ns$ ) for  $I \leq 20$  mA

\*\*  $V_{IH}(\text{Min.}) = V_{CC}+2.0V$  (Pulse Width  $\leq 8ns$ ) for  $I \leq 20$  mA

**DC AND OPERATING CHARACTERISTICS (1)**

( $0^\circ C \leq T_A \leq 70$  °C ;  $V_{CC} = 5.0V \pm 10\%$ , Unless otherwise specified)

PARAMETER	TEST CONDITIONS	SYMBOL	MIN	MAX	UNITS
Input Leakage Current	$V_{IN} = V_{SS}$ to $V_{CC}$	$IL_I$	-4	4	$\mu A$
Output Leakage Current	$/CE=V_{IH}$ or $/OE=V_{IH}$ or $/WE=V_{IL}$ $V_{OUT}=V_{SS}$ to $V_{CC}$	$IL_O$	-4	4	$\mu A$
Output High Voltage	$I_{OH} = -4.0mA$	$V_{OH}$	2.4		V
Output Low Voltage	$I_{OL} = 8.0mA$	$V_{OL}$		3.95	V

\*  $V_{CC}=5.0V \pm 5\%$ , Temp= $25$  °C

**DC AND OPERATING CHARACTERISTICS (2)**

DESCRIPTION	TEST CONDITIONS	SYMBOL	MAX			UNIT
			-10	-12	-15	
Power Supply Current: Operating	Min. Cycle, 100% Duty $/CE=V_{IL}$ , $V_{IN}=V_{IH}$ or $V_{IL}$ , $I_{OUT}=0mA$	$I_{CC}$	520	510	500	mA
Power Supply Current: Standby	Min. Cycle, $/CE=V_{IH}$	$I_{SB}$	100	100	100	mA
	$f=0MHz$ , $/CE \geq V_{CC}-0.2V$ , $V_{IN} \geq V_{CC}-0.2V$ or $V_{IN} \leq 0.2V$	$I_{SB1}$	20	20	20	mA

**CAPACITANCE**

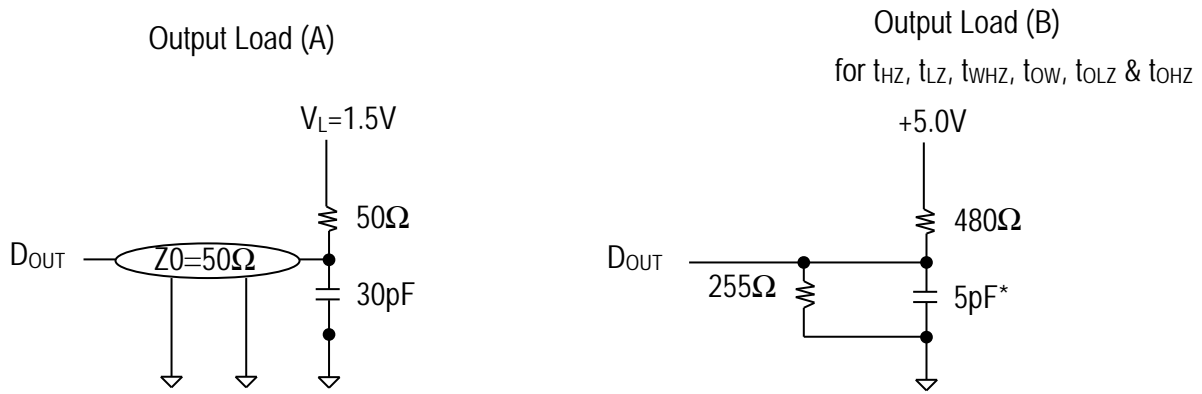
DESCRIPTION	TEST CONDITIONS	SYMBOL	MAX	UNIT
Input /Output Capacitance	$V_{I/O}=0V$	$C_{I/O}$	16	pF
Input Capacitance	$V_{IN}=0V$	$C_{IN}$	14	pF

\* **NOTE** : Capacitance is sampled and not 100% tested

**AC CHARACTERISTICS** ( $0^{\circ}\text{C} \leq T_A \leq 70^{\circ}\text{C}$ ;  $V_{CC} = 5.0\text{V} \pm 10\%$ , unless otherwise specified)

PARAMETER	VALUE
Input Pulse Level	0 to 3V
Input Rise and Fall Time	3ns
Input and Output Timing Reference Levels	1.5V
Output Load	See below

**TEST CONDITIONS**



**READ CYCLE**

PARAMETER	SYMBOL	-10		-12		-15		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	
Read Cycle Time	$t_{RC}$	10	-	12	-	15	-	ns
Address Access Time	$t_{AA}$	-	10	-	12	-	15	ns
Chip Select to Output	$t_{CO}$	-	10	-	12	-	15	ns
Output Enable to Valid Output	$t_{OE}$	-	5	-	6	-	7	ns
/BS0 ~ /BS3 Access Time	$t_{BA}$	-	5	-	6	-	7	ns
Chip Enable to Low-Z Output	$t_{LZ}$	3	-	3	-	3	-	ns
Output Enable to Low-Z Output	$t_{OLZ}$	0	-	0	-	0	-	ns
/BS0 ~ /BS3 Enable to Low-Z Output	$t_{BHZ}$	0	-	0	-	0	-	ns
Chip Disable to High-Z Output	$t_{HZ}$	0	5	0	6	0	7	ns
Output Disable to High-Z Output	$t_{OHZ}$	0	5	0	6	0	7	
/BS0 ~ /BS3 Disable to High-Z Output	$t_{BHZ}$	0	5	0	6	0	7	Ns
Output Hold from address Change	$t_{OH}$	3	-	3	-	3	-	Ns

**WRITE CYCLE**

PARAMETER	SYMBOL	-10		-12		-15		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	
Write Cycle Time	$t_{WC}$	10	-	12	-	15	-	ns
Chip Select to End of Write	$t_{CW}$	7	-	8	-	10	-	ns
Address Set-up Time	$t_{AS}$	0	-	0	-	0	-	ns
Address Valid to End of Write	$t_{AW}$	7	-	8	-	10	-	ns
Write Pulse Width (/OE High)	$t_{WP}$	7	-	8	-	10	-	ns
Write Pulse Width (/OE Low)	$t_{WP1}$	10	-	12	-	15	-	ns
Write Recovery Time	$t_{WR}$	0	-	0	-	0	-	ns
Write to Output High-Z	$t_{WHZ}$	0	5	0	6	0	7	ns
Data to Write Time Overlap	$t_{DW}$	5	-	6	-	7	-	ns
Data Hold from Write Time	$t_{DH}$	0	-	0	-	0	-	ns
End of Write to Output Low-Z	$t_{OW}$	3	-	3	-	3	-	ns

**TIMING DIAGRAMS**

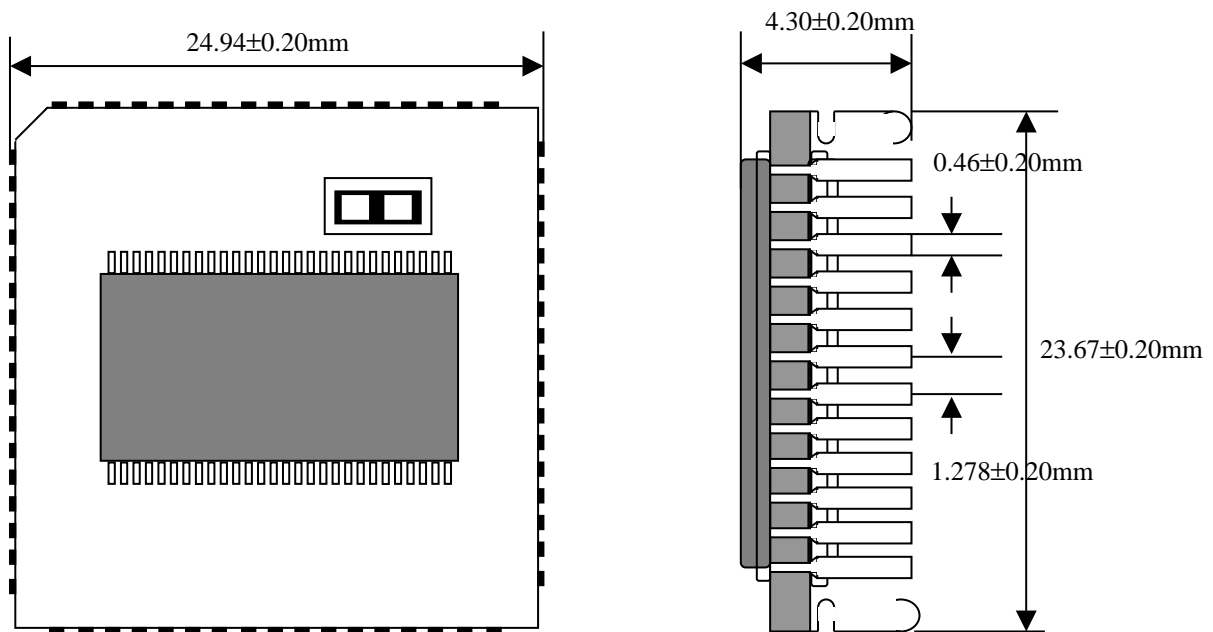
Please refer to timing diagram chart.

**FUNCTIONAL DESCRIPTION**

/CE	/WE	/OE	MODE	I/O PIN	SUPPLY CURRENT
H	X*	X	Not Select	High-Z	$I_{SB}, I_{SB1}$
L	H	H	Output Disable	High-Z	$I_{CC}$
L	H	L	Read	$D_{OUT}$	$I_{CC}$
L	L	X	Write	$D_{IN}$	$I_{CC}$

Note: X means Don't Care

## PACKAGING DIMENSIONS



## ORDERING INFORMATION

Part Number	Density	Org.	Package	Component Number	Vcc	Access Time
HMS25632J2-10	1MByte	256KX 32bit	68 Pin-JLCC	2EA	5V	10ns
HMS25632J2-12	1MByte	256KX 32bit	68 Pin-JLCC	2EA	5V	12ns
HMS25632J2-15	1MByte	256KX 32bit	68 Pin-JLCC	2EA	5V	15ns
HMS25632J2-55	1MByte	256KX 32bit	68 Pin-JLCC	2EA	5V	55ns